



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	2Ω @ $V_{GS} = 4.5V$	350mA
60 V	2.5Ω @ $V_{GS} = 2.5V$	SSUIIA

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- **Power Management Functions**

Features

- **Dual N-Channel MOSFET**
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

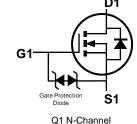
- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

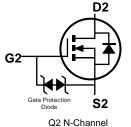


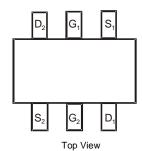


Top View

SOT363







Pin out

Equivalent Circuit

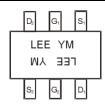
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN62D0UDW-7	SOT363	3000/Tape & Reel
DMN62D0UDW-13	SOT363	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



LEE = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Date Code IV	~,											
Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	Е	F	G	Н		J	K	L	M
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Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

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Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	I _D	350 290	mA		
Maximum Continuous Body Diode Forward Current	(Note 6)		Is	0.4	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	320	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	400	°C/W
Total Power Dissipation (Note 6)		P_D	410	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	312	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

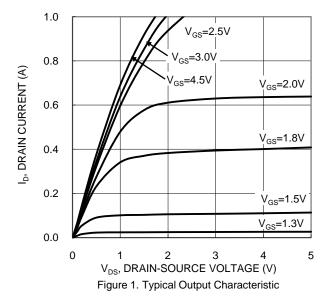
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

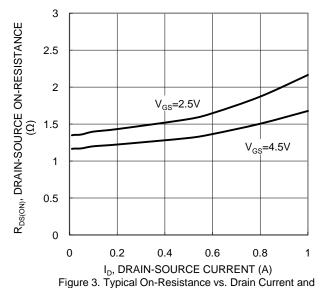
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	_		V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_		1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	1.0	V	$V_{DS} = 10V, I_D = 250\mu A$
			1.2	2.0		$V_{GS} = 4.5V, I_D = 0.1A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	1.4	2.5	Ω	$V_{GS} = 2.5V, I_D = 0.05A$
			1.8	3.0		$V_{GS} = 1.8V, I_D = 0.05A$
Forward Transconductance	Y _{fs}	_	1.8	_	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V _{SD}	_	0.8	1.3	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	32	_	pF	.,
Output Capacitance	Coss	_	3.9	_	pF	V _{DS} = 30V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	2.4	_	pF	1 = 1.0W112
Gate Resistance	Rg	_	101	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$
Total Gate Charge	Qg	_	0.5	_	nC	45)/)/ 40)/
Gate-Source Charge	Q_{gs}	_	0.09	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	Q _{qd}	_	0.09	_	nC	I _D = 250mA
Turn-On Delay Time	t _{D(ON)}	_	2.4	_	ns	
Turn-On Rise Time	t _R	_	2.5	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$
Turn-Off Delay Time	t _{D(OFF)}	_	22.6	_	ns	$R_G = 25\Omega$, $I_D = 200mA$
Turn-Off Fall Time	t _F	_	12.5	_	ns	

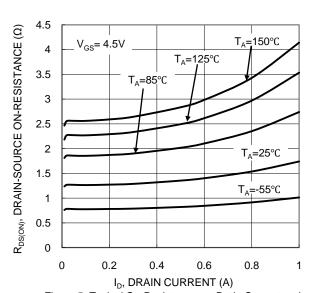
Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.



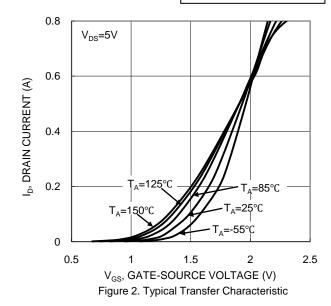


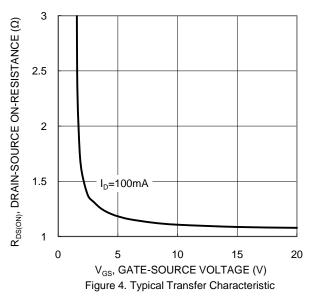




Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Temperature





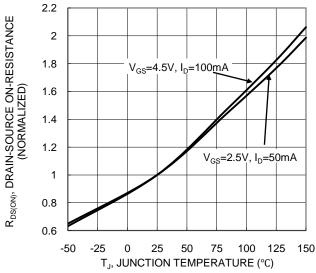


Figure 6. On-Resistance Variation with Junction Temperature



DMN62D0UDW

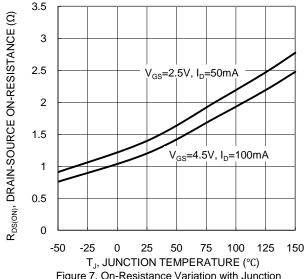
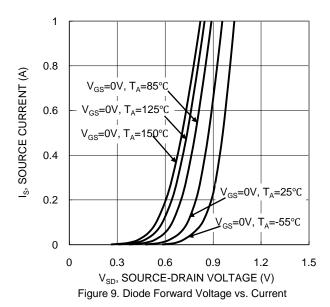
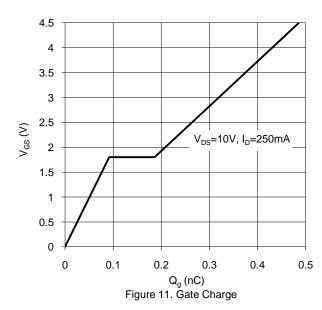
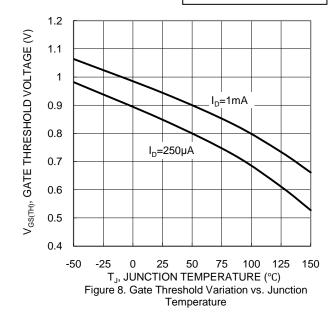
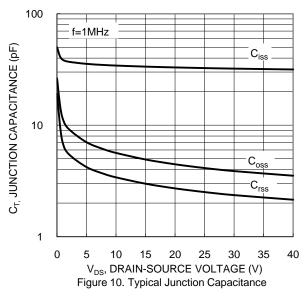


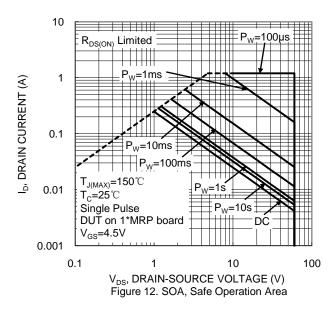
Figure 7. On-Resistance Variation with Junction
Temperature



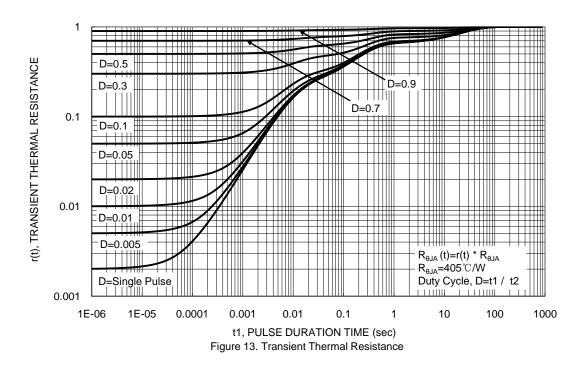






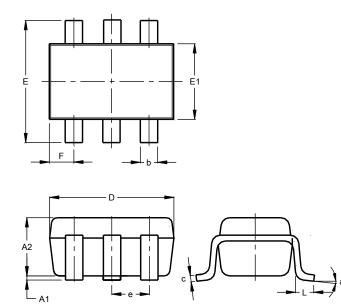






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

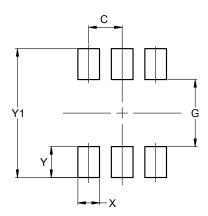


SOT363								
Dim	Min Max Typ							
A1	0.00	0.10	0.05					
A2	0.90	1.00	1.00					
b	0.10	0.30	0.25					
С	0.10	0.22	0.11					
D	1.80	2.20	2.15					
E	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	0.650 BSC							
F	0.40	0.45	0.425					
L	0.25	0.40	0.30					
а	8°							
All Dimensions in mm								



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.650		
G	1.300		
X	0.420		
Υ	0.600		
Y1	2.500		

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